SN74AUP1G08 Low-Power Single 2-Input Positive-AND Gate

1 Features

- Available in the Ultra Small 0.64 mm² Package (DPW) With 0.5-mm Pitch
- Low Static-Power Consumption:
 I_{CC} = 0.9 μA Maximum
- Low Dynamic-Power Consumption: C_{pd} = 4.3 pF Typical at 3.3 V
- Low Input Capacitance: C_i = 1.5 pF Typical
- Low Noise: Overshoot and Undershoot <10% of V_{CC}
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back Drive Protection
- Schmitt-Trigger Action Allows Slow Input Transition and Better Switching Noise Immunity at the Input (V_{hys} = 250 mV Typical at 3.3 V)
- Wide Operating V_{CC} Range of 0.8 V to 3.6 V
- · Optimized for 3.3-V Operation
- 3.6-V I/O Tolerant to Support Mixed-Mode Signal Operation
- t_{pd} = 4.3 ns Maximum at 3.3 V
- · Suitable for Point-to-Point Applications
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

Simplified Schematic



2 Applications

- ATCA Solutions
- Active Noise Cancellation (ANC)
- Barcode Scanner
- Blood Pressure Monitor
- CPAP Machine
- Cable Solutions
- DLP 3D Machine Vision, Hyperspectral Imaging, Optical Networking, and Spectroscopy
- E-Book
- Embedded PC
- Field Transmitter: Temperature or Pressure Sensor
- Fingerprint Biometrics
- HVAC: Heating, Ventilating, and Air Conditioning
- Network-Attached Storage (NAS)
- Server Motherboard and PSU
- Software Defined Radio (SDR)
- TV: High-Definition (HDTV), LCD, and Digital
- Video Communications System
- Wireless Data Access Card, Headset, Keyboard, Mouse, and LAN Card
- X-ray: Baggage Scanner, Medical, and Dental

3 Description

This single 2-input positive-AND gate is designed for 0.8-V to 3.6-V V_{CC} operation and performs the Boolean function $Y = A \bullet B$ or $Y = \overline{A + B}$ in positive logic.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74AUP1G08DBV	SOT-23 (5)	2.90 mm × 1.60 mm
SN74AUP1G08DRL	SOT (5)	1.60 mm × 1.20 mm
SN74AUP1G08DRY	SON (6)	1.45 mm × 1.00 mm
SN74AUP1G08DPW	X2SON (5)	0.80 mm × 0.80 mm
SN74AUP1G08YZP	DSBGA (5)	1.37 mm × 0.88 mm
SN74AUP1G08DCK	SC70 (5)	1.25 mm x 2.00 mm
SN74AUP1G08DSF	SON (6)	1.00 mm x 1.00 mm
SN74AUP1G08YFP	DSBGA (6)	1.16 mm x 0.76 mm

⁽¹⁾ For all available packages, see the orderable addendum at the end of the data sheet.

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	•			
A	dded temperature ranges for Storage temperature, T_{stg} and	Junctio	n temperature, T _J in <i>Absolute Maximum Rating</i> s	; <mark>5</mark>
С	hanged Handling Ratings to ESD Ratings and changed MIN	N, MAX	column to a VALUE column	5
A	dded Receiving Notification of Documentation Updates sect	tion		15
han	ges from Revision N (November 2012) to Revision O			Page
U	pdated document to new TI data sheet format			1
	emoved ordering information.			
A	dded Applications			1
Fi	xed typo in YFP package drawing			4
Α	dded Handling Ratings table			5

Added Thermal Information table. 6
Added Typical Characteristics. 9

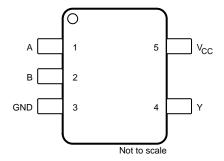
Changes from Revision M (September 2012) to Revision N

SN74AUP1G08

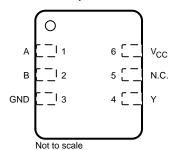
Ch	anges from Revision K (October 2011) to Revision L	Page
•	Revised document to fix package addendum issue.	·

5 Pin Configuration and Functions

DRL, DCK, or DBV Packages 5-Pin SOT, SC70, or SOT-23 Top View

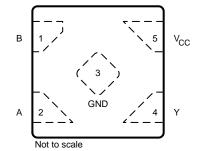


DRY or DSF Packages 6-Pin SON Top View

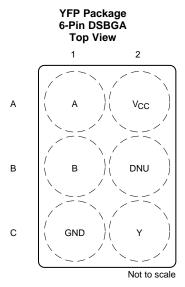


N.C. - No internal connection

DPW Package 5-PIN X2SON Top View

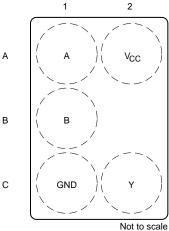


See mechanical drawings for dimensions.



DNU - Do not use





Pin Functions

		PIN					
NAME	DRL, DCK, DBV	DPW	DRY, DSF	YZP	YFP	I/O	DESCRIPTION
Α	1	2	1	A1	A1	I	Input A
В	2	1	2	B1	B1	I	Input B
DNU	_	_	_	-	B2	_	Do not use
GND	3	3	3	C1	C1	_	Ground
N.C.	_	_	5	-	_	_	No internal connection
V_{CC}	5	5	6	A2	A2	_	Power Pin
Υ	4	4	4	C2	C2	0	Output Y

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	4.6	V
VI	Input voltage ⁽²⁾		-0.5	4.6	V
Vo	Voltage range applied to any output in the high-i	mpedance or power-off state (2)	-0.5	4.6	V
Vo	Output voltage range in the high or low state (2)			V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±20	mA
	Continuous current through V _{CC} or GND			±50	mA
TJ	Maximum junction temperature			150	°C
T _{stg}	Storage temperature			150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

	•			
			VALUE	UNIT
\/	Clastractatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	V
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 (2)	1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		0.8	3.6	V
		V _{CC} = 0.8 V	V _{CC}		
.,	Himb lavel input valtage	V _{CC} = 1.1 V to 1.95 V	0.65 × V _{CC}		.,
V _{IH}	High-level input voltage	V _{CC} = 2.3 V to 2.7 V	1.6		V
		V _{CC} = 3 V to 3.6 V	2		

²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT	
		$V_{CC} = 0.8 \text{ V}$		0		
V_{IL}	Low lovel input voltage	$V_{CC} = 1.1 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	V	
	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.9		
V_{I}	Input voltage		0	3.6	V	
Vo	Output voltage		0	V _{CC}	V	
		V _{CC} = 0.8 V		-20	μΑ	
	High-level output current	V _{CC} = 1.1 V		-1.1		
		V _{CC} = 1.4 V		-1.7	mA	
I _{OH}		V _{CC} = 1.65		-1.9		
		V _{CC} = 2.3 V		-3.1		
		V _{CC} = 3 V		-4		
		V _{CC} = 0.8 V		20	μΑ	
		V _{CC} = 1.1 V		1.1		
	Laur laural autout auronat	V _{CC} = 1.4 V	.4 V		1	
I _{OL}	Low-level output current	V _{CC} = 1.65 V		1.9	mA	
		V _{CC} = 2.3 V		3.1		
		V _{CC} = 3 V		4		
Δt/Δν	Input transition rise or fall rate	V _{CC} = 0.8 V to 3.6 V		200	ns/V	
T _A	Operating free-air temperature	·	-40	85	°C	

6.4 Thermal Information

••••								
		SN74AUP1G08						
THERMAL METRIC ⁽¹⁾		DBV (SOT-23)	DCK (SC70)	DRL (SOT)	DSF (SON)	DRY (SON)	DPW (X2SON)	UNIT
			5 PINS	5 PINS	6 PINS	6 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	298.6	314.4	349.7	407.1	554.9	291.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	240.2	128.7	120.5	232	385.4	224.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	134.6	100.6	171.4	306.9	388.2	245.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	114.5	7.1	10.8	40.3	159	245.6	°C/W
ΨЈВ	Junction-to-board characterization parameter	133.9	99.8	169.4	306	384.1	195.4	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A	= 25°C	T _A = -40°C to +85°C	LINUT
			MIN	TYP MAX	MIN MAX	UNIT
	I _{OH} = -20 μA	0.8 V to 3.6 V	V _{CC} - 0.1		V _{CC} - 0.1	
	I _{OH} = -1.1 mA	1.1 V	0.75 × V _{CC}		0.7 × V _{CC}	
	I _{OH} = -1.7 mA	1.4 V	1.11		1.03	
V_{OH}	I _{OH} = -1.9 mA	1.65 V	1.32		1.3	V
	I _{OH} = -2.3 mA	221/	2.05		1.97	
	I _{OH} = -3.1 mA	2.3 V	1.9		1.85	
	$I_{OH} = -2.7 \text{ mA}$	2.1/	2.72		2.67	
	$I_{OH} = -4 \text{ mA}$	3 V	2.6		2.55	
	I _{OL} = 20 μA	0.8 V to 3.6 V		0.1	0.1	
	I _{OL} = 1.1 mA	1.1 V		0.3 × V _{CC}	0.3 × V _{CC}	
	I _{OL} = 1.7 mA	1.4 V		0.31	0.37	
V_{OL}	I _{OL} = 1.9 mA	1.65 V		0.31	0.35	V
OL .	I _{OL} = 2.3 mA	2.3 V		0.31	0.33	
	I _{OL} = 3.1 mA			0.44	0.45	
	I _{OL} = 2.7 mA			0.31	0.33	
	I _{OL} = 4 mA	3 V		0.44	0.45	
I _I A or B input	V _I = GND to 3.6 V	0 V to 3.6 V		0.1	0.5	μA
I _{off}	V_1 or $V_0 = 0$ V to 3.6 V	0 V		0.2	0.6	μA
Δl _{off}	V_I or $V_O = 0$ V to 3.6 V	0 V to 0.2 V		0.2	0.6	μA
Icc	$V_I = GND \text{ or}$ $(V_{CC} \text{ to } 3.6 \text{ V})$ $I_O = 0$	0.8 V to 3.6 V		0.5	0.9	μA
ΔI_{CC}	$V_I = V_{CC} - 0.6 V^{(1)}$ $I_O = 0$	3.3 V		40	50	μA
0	V V OND	0 V		1.5		
C _i	$V_I = V_{CC}$ or GND	3.6 V		1.5		pF
C _o	V _O = GND	0 V		3		pF

⁽¹⁾ One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

6.6 Switching Characteristics, $C_L = 5 pF$

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3 and Figure 4)

PARAMETER	FROM	FROM TO	V	T _A = 25°C			$T_A = -40$ °C to	UNIT	
	(INPUT)	(OUTPUT)	V _{CC}	MIN	TYP	MAX	MIN	MAX	UNIT
			0.8 V		18				
	A or B	A or B Y	1.2 V ± 0.1 V	2.6	7.3	12.8	2.1	15.6]
			1.5 V ± 0.1 V	1.4	5.2	8.7	0.9	10.3	no
t _{pd}			1.8 V ± 0.15 V	1	4.2	6.6	0.5	8.2	ns
			2.5 V ± 0.2 V	1	3	4.4	0.5	5.5	
			3.3 V ± 0.3 V	1	2.4	3.5	0.5	4.3	

6.7 Switching Characteristics, $C_L = 10 pF$

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3 and Figure 4)

PARAMETER	FROM	TO (OUTPUT)	V	T _A = 25°C			$T_A = -40^{\circ}C$ to	+85°C	UNIT
PARAMETER	(INPUT)		V _{CC}	MIN	TYP	MAX	MIN	MAX	UNIT
			0.8 V		21				
		1.2 V ± 0.1 V	1.5	8.5	14.7	1	17.2		
		Y	1.5 V ± 0.1 V	1	6.2	10	0.5	11.3	20
t _{pd}	A or B		1.8 V ± 0.15 V	1	5	7.7	0.5	9	ns
			$2.5 \text{ V} \pm 0.2 \text{ V}$	1	3.6	5.2	0.5	6.1	
			$3.3 \text{ V} \pm 0.3 \text{ V}$	1	2.9	4.2	0.5	4.7	

6.8 Switching Characteristics, $C_L = 15 pF$

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3 and Figure 4)

DADAMETED	FROM	TO (OUTPUT)	V	T _A	= 25°C		$T_A = -40^{\circ}C$ to	UNIT	
PARAMETER	(INPUT)		V _{CC}	MIN	TYP	MAX	MIN	MAX	UNIT
			0.8 V		24				
		Y	1.2 V ± 0.1 V	3.6	9.9	16.3	3.1	19.9	
	A or B		1.5 V ± 0.1 V	2.3	7.2	11.1	1.8	13.2	
t _{pd}	AUIB		1.8 V ± 0.15 V	1.6	5.8	8.7	1.1	10.6	ns
			2.5 V ± 0.2 V	1	4.3	5.9	0.5	7.3	
			3.3 V ± 0.3 V	1	3.4	4.8	0.5	5.9	

6.9 Switching Characteristics, $C_L = 30 pF$

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3 and Figure 4)

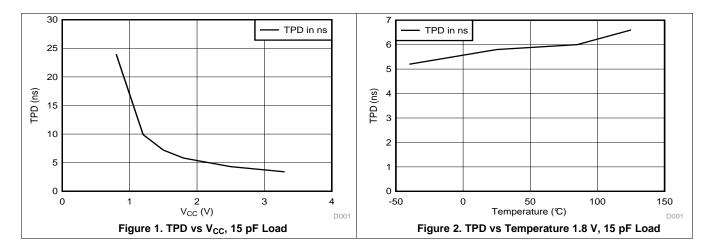
PARAMETER	FROM	TO (OUTPUT)	V _{cc}	T _A	= 25°C		T _A = -40° +85°	°C to	UNIT
	(INPUT)	(001701)		MIN	TYP	MAX	MIN	MAX	
			0.8 V		32.8				
	A or B	Υ	1.2 V ± 0.1 V	4.9	13.1	20.9	4.4	25.5	
			1.5 V ± 0.1 V	3.4	9.5	14.2	2.9	16.9	
t _{pd}			1.8 V ± 0.15 V	2.5	7.7	11	2	13.5	ns
			2.5 V ± 0.2 V	1.8	5.7	7.6	1.3	9.4	
			3.3 V ± 0.3 V	1.5	4.7	6.2	1	7.5	

6.10 Operating Characteristics

 $T_A = 25$ °C

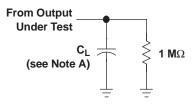
	PARAMETER	TEST CONDITIONS	V _{cc}	TYP	UNIT
			0.8 V	4	
			1.2 V ± 0.1 V	4	
<u></u>	Dower dissinction conscitance	f _ 10 M⊔ 7	1.5 V ± 0.1 V	4	pF
C _{pd}	Power dissipation capacitance	f = 10 MHz	1.8 V ± 0.15 V	4	þΓ
			2.5 V ± 0.2 V	4.1	
			3.3 V ± 0.3 V	4.3	

6.11 Typical Characteristics



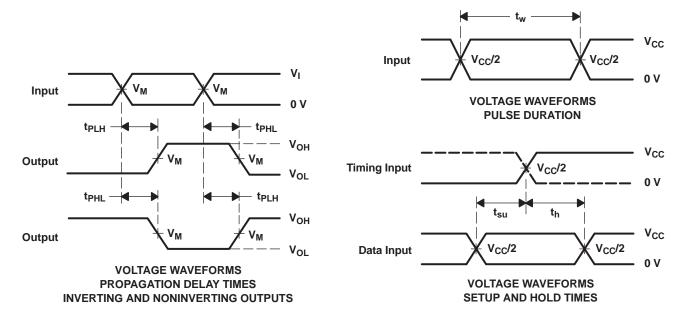
7 Parameter Measurement Information

7.1 Propagation Delays, Setup and Hold Times, and Pulse Duration



LOAD CIRCUIT

	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V_{CC} = 1.8 V \pm 0.15 V	V_{CC} = 2.5 V \pm 0.2 V	V _{CC} = 3.3 V ± 0.3 V
C _L V _M	5, 10, 15, 30 pF V _{CC} /2 V _{CC}	5, 10, 15, 30 pF V _{CC} /2 V _{CC}	5, 10, 15, 30 pF V _{CC} /2 V _{CC}	5, 10, 15, 30 pF V _{CC} /2 V _{CC}	5, 10, 15, 30 pF V _{CC} /2 V _{CC}	5, 10, 15, 30 pF V _{CC} /2 V _{CC}

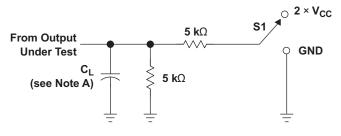


NOTES: A. C_L includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, slew rate \geq 1 V/ns.
- C. The outputs are measured one at a time, with one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{pd} .
- E. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

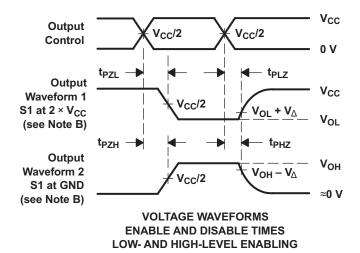
7.2 Enable and Disable Times



TEST	S1
t_{PLZ}/t_{PZL}	2 × V _{CC}
t_{PHZ}/t_{PZH}	GND

LOAD CIRCUIT

	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 3.3 V ± 0.3 V
C _L V _M V _I	5, 10, 15, 30 pF V _{CC} /2 V _{CC} 0.1 V	5, 10, 15, 30 pF V _{CC} /2 V _{CC} 0.1 V	5, 10, 15, 30 pF V _{CC} /2 V _{CC} 0.1 V	5, 10, 15, 30 pF V _{CC} /2 V _{CC} 0.15 V	5, 10, 15, 30 pF V _{CC} /2 V _{CC} 0.15 V	5, 10, 15, 30 pF V _{CC} /2 V _{CC} 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR≤ 10 MHz, Z_O = 50 Ω, slew rate ≥ 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

This single 2-input positive-AND gate is designed for 0.8-V to 3.6-V V_{CC} operation and performs the Boolean function $Y = A \bullet B$ or $Y = \overline{A + B}$ in positive logic.

The AUP family of devices has quiescent power consumption less than 1 μ A and comes in the ultra small DPW package. The DPW package technology is a major breakthrough in IC packaging. Its tiny 0.64 mm² square footprint saves significant board space over other package options while still retaining the traditional manufacturing friendly lead pitch of 0.5 mm.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered. The I_{off} feature also allows for live insertion.

8.2 Functional Block Diagram



8.3 Feature Description

- Wide operating V_{CC} range of 0.8 V to 3.6 V
- 3.6-V I/O tolerant to support down translation
- Input hysteresis allows slow input transition and better switching noise immunity at the input
- I_{off} feature allows voltages on the inputs and outputs when V_{CC} is 0 V
- · Low noise due to slower edge rates

8.4 Device Functional Modes

Table 1. Function Table

INP	UTS	OUTPUT
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

9 Application and Implementation

9.1 Application Information

The AUP family is TI's premier solution to the industry's low-power needs in battery-powered portable applications. This family ensures a very low static and dynamic power consumption across the entire V_{CC} range of 0.8 V to 3.6 V, resulting in an increased battery life. This product also maintains excellent signal integrity. It has a small amount of hysteresis built in allowing for slower or noisy input signals. The lowered drive produces slower edges and prevents overshoot and undershoot on the outputs.

The AUP family of single gate logic makes excellent translators for the new lower voltage Micro- processors that typically are powered from 0.8~V to 1.2~V. They can drop the voltage of peripheral drivers and accessories that are still powered by 3.3~V to the new μ C power levels.

9.2 Typical Application

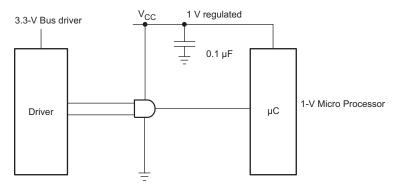


Figure 5. Typical Application Schematic

9.2.1 Design Requirements

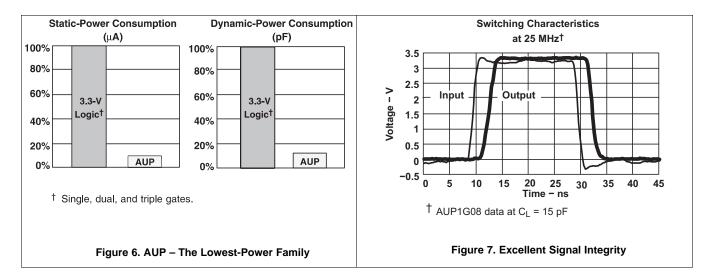
SN74AUP1G08 device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits.

9.2.2 Detailed Design Procedure

- 1. Recommended Input conditions
 - Rise time and fall time specifications. See (Δt/ΔV) in Recommended Operating Conditions table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as 3.6 V at any valid V_{CC}
- 2. Recommended output conditions
 - Load currents should not exceed 20 mA on the output and 50 mA total for the part
 - Outputs should not be pulled above V_{CC}

Typical Application (continued)

9.2.3 Application Curves



10 Power Supply Recommendations

The power supply can be any voltage between the Min and Max supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μ F is recommended and if there are multiple V_{CC} terminals then 0.01 μ F or 0.022 μ F is recommended for each power terminal. It is ok to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified in Figure 8 are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or $V_{\rm CC}$ whichever make more sense or is more convenient. It is generally OK to float outputs unless the part is a transceiver. If the transceiver has an output enable pin it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

11.2 Layout Example



Figure 8. Layout Diagram

12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates — go to the product folder for your device on ti.com. In the upper right-hand corner, click the *Alert me* button to register and receive a weekly digest of product information that has changed (if any). For change details, check the revision history of any revised document.

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AUP1G08DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(H08F, H08R)	Samples
SN74AUP1G08DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	H08R	Samples
SN74AUP1G08DBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	H08R	Samples
SN74AUP1G08DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(HE5, HEF, HEK, HE R) (HEH, HEP, HES)	Samples
SN74AUP1G08DCKRE4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(HE5, HEF, HEK, HE R) (HEH, HEP, HES)	Samples
SN74AUP1G08DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(HE5, HEF, HEK, HE R) (HEH, HEP, HES)	Samples
SN74AUP1G08DCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(HE5, HER)	Samples
SN74AUP1G08DPWR	ACTIVE	X2SON	DPW	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	E4	Samples
SN74AUP1G08DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(HE7, HER)	Samples
SN74AUP1G08DRY2	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HE	Samples
SN74AUP1G08DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	HE	Samples
SN74AUP1G08DSF2	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(HE, HER) HEH	Samples
SN74AUP1G08DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(HE, HER) HEH	Samples
SN74AUP1G08YFPR	ACTIVE	DSBGA	YFP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM		HEN	Samples
SN74AUP1G08YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	HEN	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PACKAGE OPTION ADDENDUM

6-Sep-2021

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

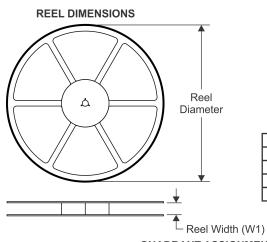
OTHER QUALIFIED VERSIONS OF SN74AUP1G08:

Automotive: SN74AUP1G08-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



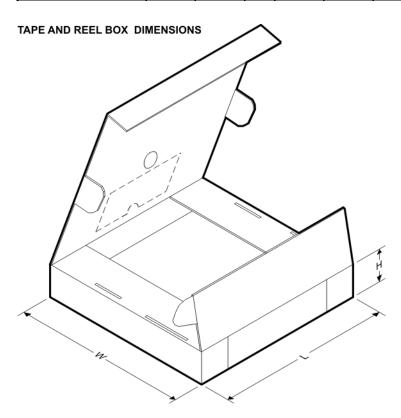
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUP1G08DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUP1G08DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUP1G08DBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUP1G08DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AUP1G08DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AUP1G08DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AUP1G08DCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AUP1G08DPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q3
SN74AUP1G08DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74AUP1G08DRLR	SOT-5X3	DRL	5	4000	180.0	9.5	1.78	1.78	0.69	4.0	8.0	Q3
SN74AUP1G08DRY2	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q3
SN74AUP1G08DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74AUP1G08DRYR	SON	DRY	6	5000	180.0	8.4	1.25	1.6	0.7	4.0	8.0	Q1
SN74AUP1G08DSF2	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.63	4.0	8.0	Q3
SN74AUP1G08DSF2	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q3
SN74AUP1G08DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74AUP1G08DSFR	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.63	4.0	8.0	Q2
SN74AUP1G08YFPR	DSBGA	YFP	6	3000	178.0	9.2	0.89	1.29	0.62	4.0	8.0	Q1

PACKAGE MATERIALS INFORMATION

24-Jul-2020

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUP1G08YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUP1G08DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74AUP1G08DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AUP1G08DBVT	SOT-23	DBV	5	250	202.0	201.0	28.0
SN74AUP1G08DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AUP1G08DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74AUP1G08DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74AUP1G08DCKT	SC70	DCK	5	250	202.0	201.0	28.0
SN74AUP1G08DPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
SN74AUP1G08DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74AUP1G08DRLR	SOT-5X3	DRL	5	4000	184.0	184.0	19.0
SN74AUP1G08DRY2	SON	DRY	6	5000	184.0	184.0	19.0
SN74AUP1G08DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74AUP1G08DRYR	SON	DRY	6	5000	202.0	201.0	28.0
SN74AUP1G08DSF2	SON	DSF	6	5000	202.0	201.0	28.0
SN74AUP1G08DSF2	SON	DSF	6	5000	184.0	184.0	19.0
SN74AUP1G08DSFR	SON	DSF	6	5000	184.0	184.0	19.0

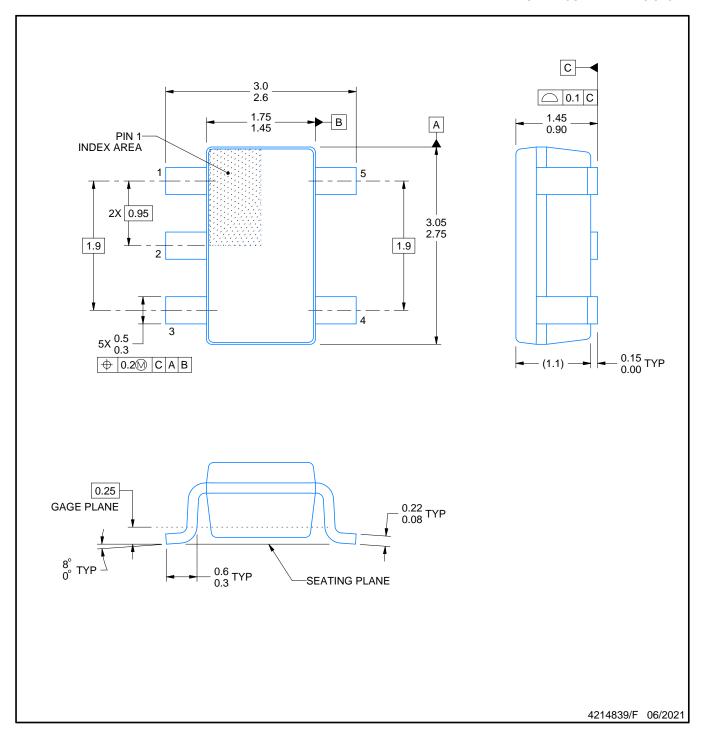
PACKAGE MATERIALS INFORMATION

24-Jul-2020

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUP1G08DSFR	SON	DSF	6	5000	202.0	201.0	28.0
SN74AUP1G08YFPR	DSBGA	YFP	6	3000	220.0	220.0	35.0
SN74AUP1G08YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE TRANSISTOR



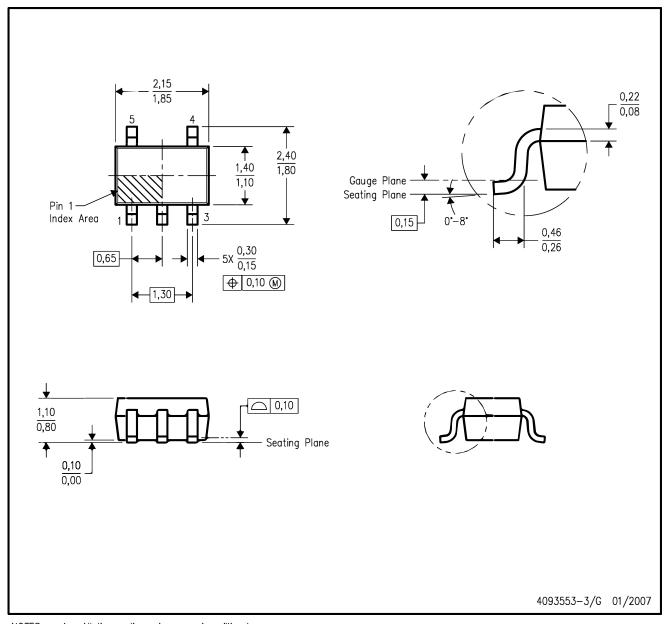
NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE

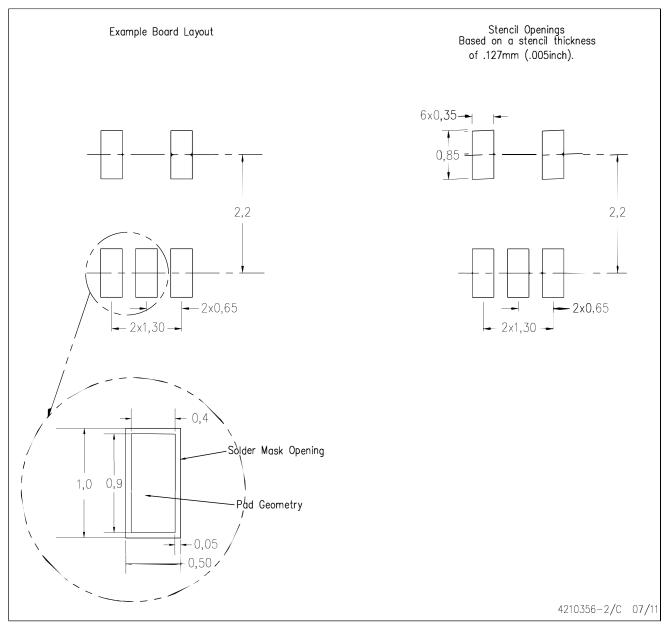


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.

DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE

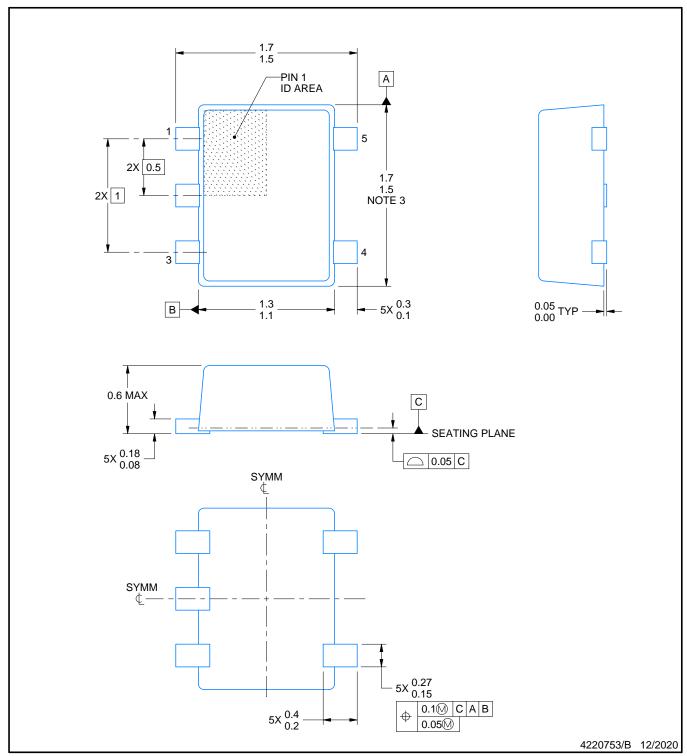


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1

PLASTIC SMALL OUTLINE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

PLASTIC SMALL OUTLINE



NOTES: (continued)

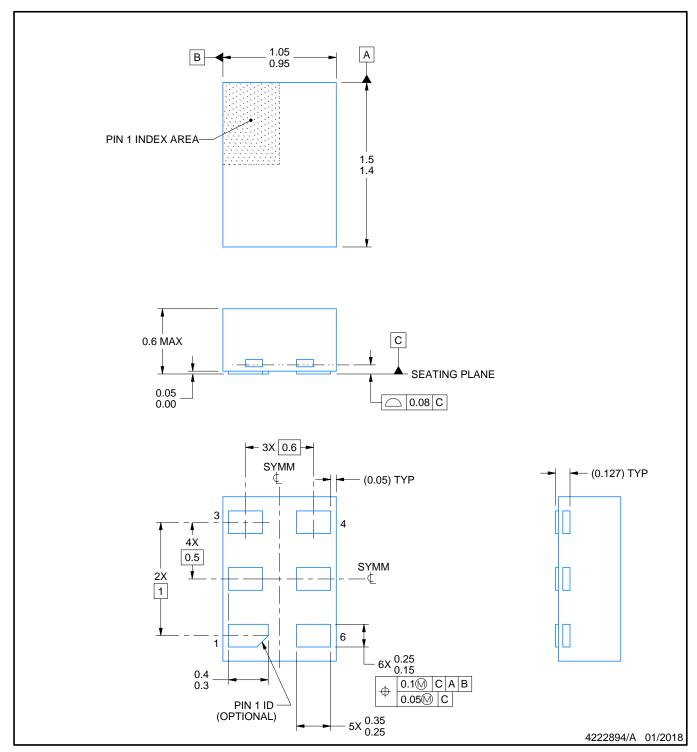
^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

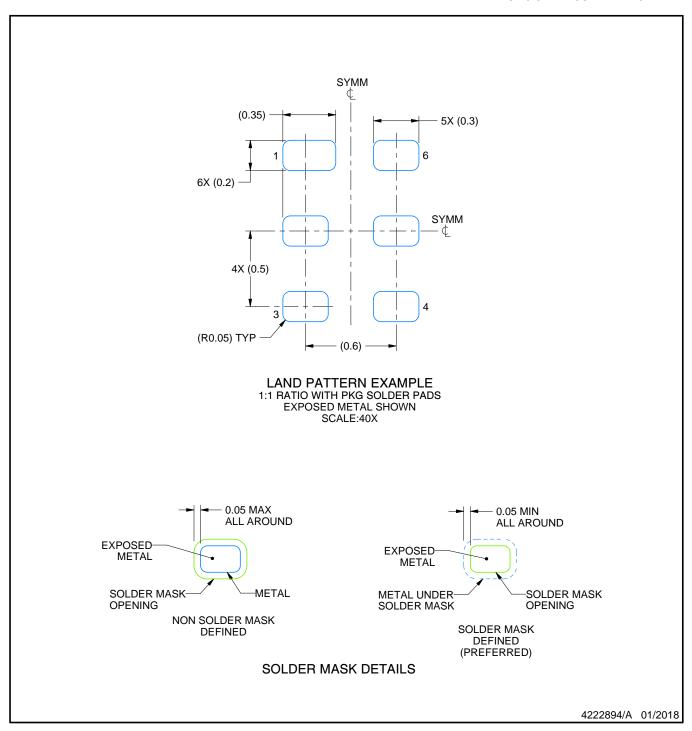




NOTES:

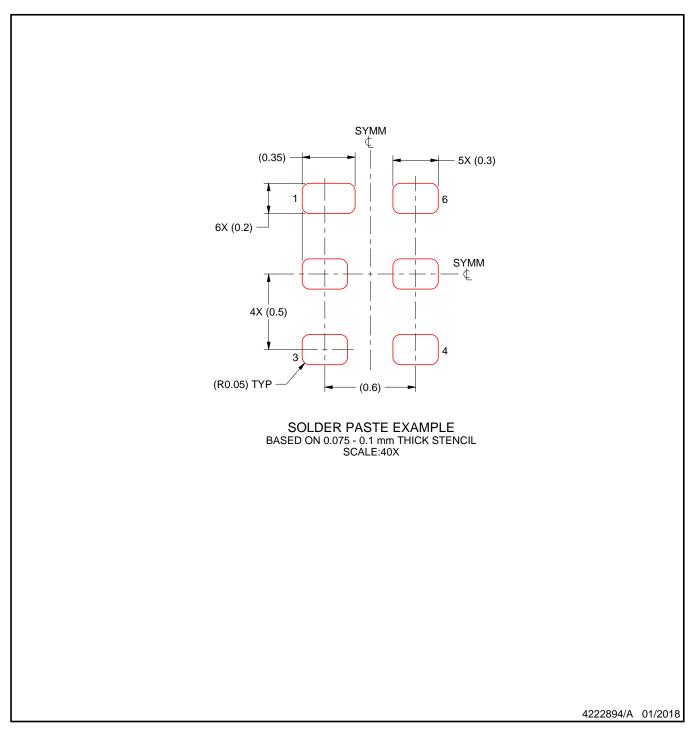
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



NOTES: (continued)

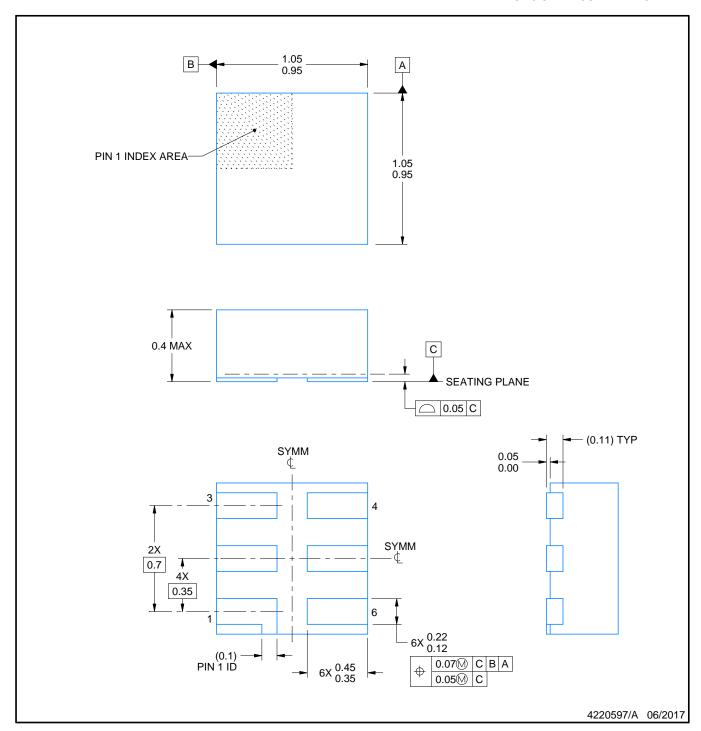
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



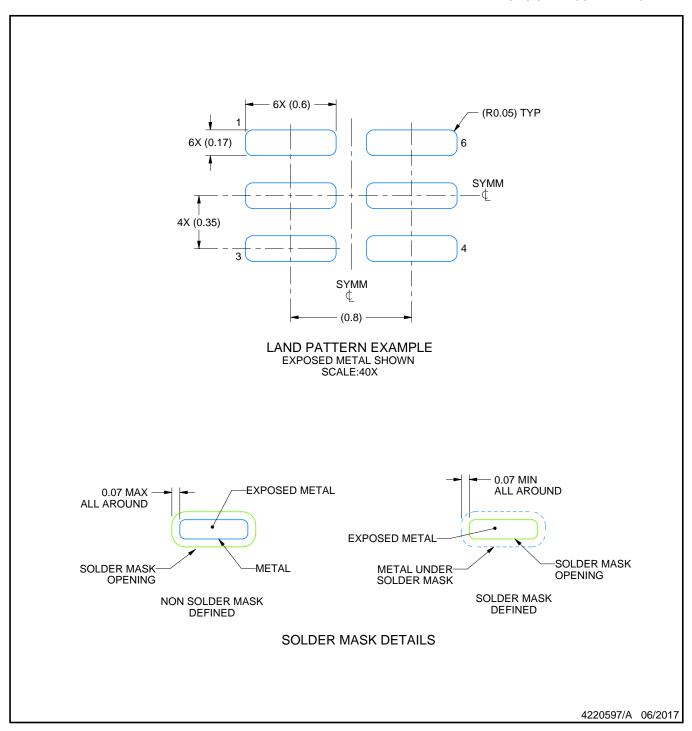


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

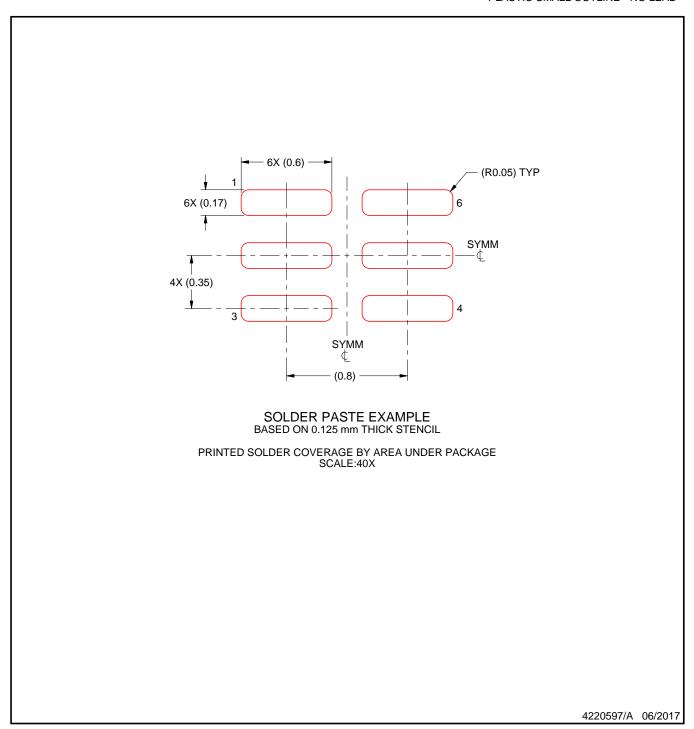
 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.



NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

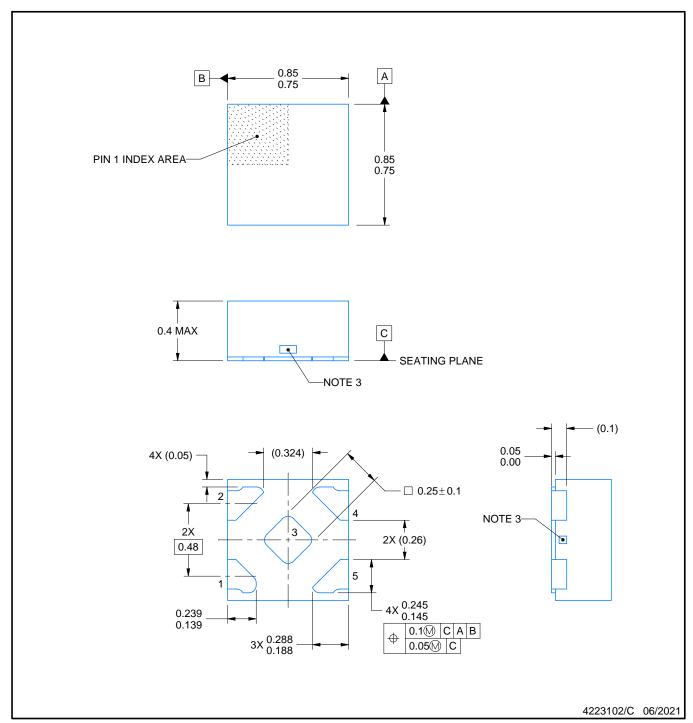


4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

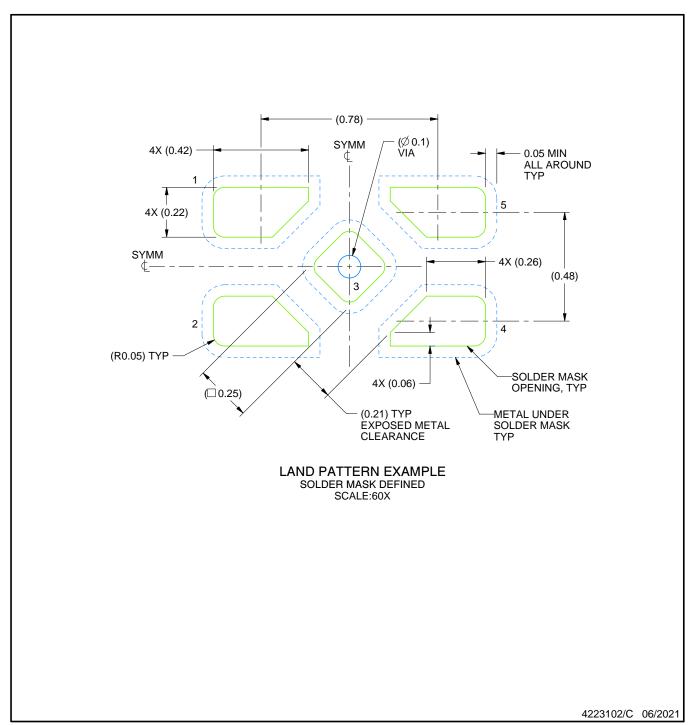




NOTES:

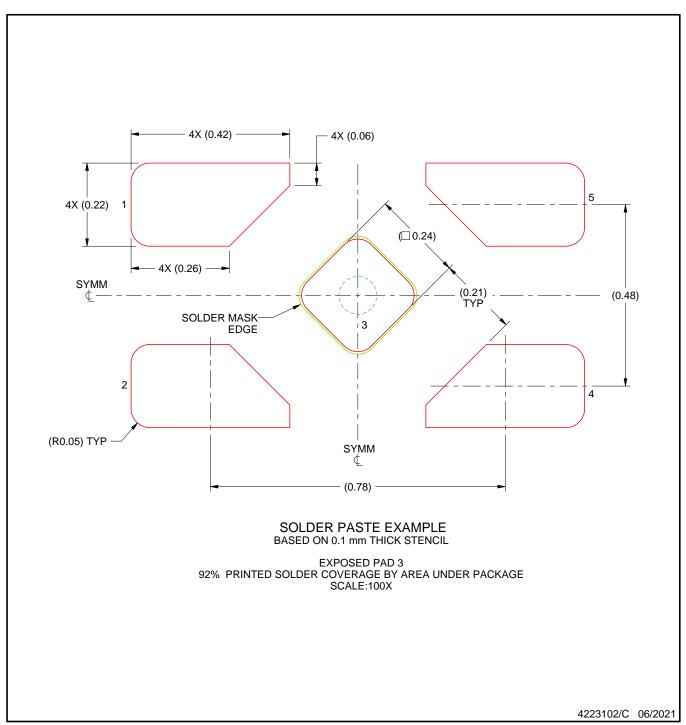
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

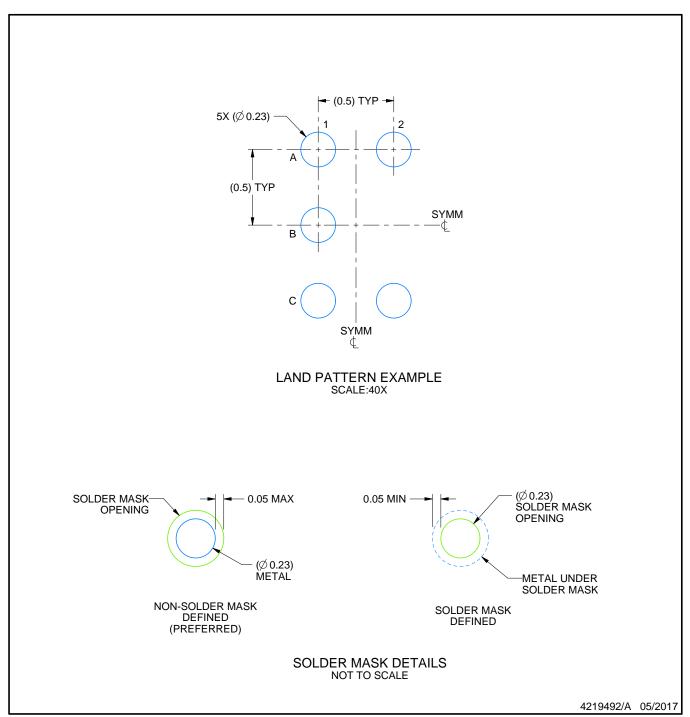




NOTES:

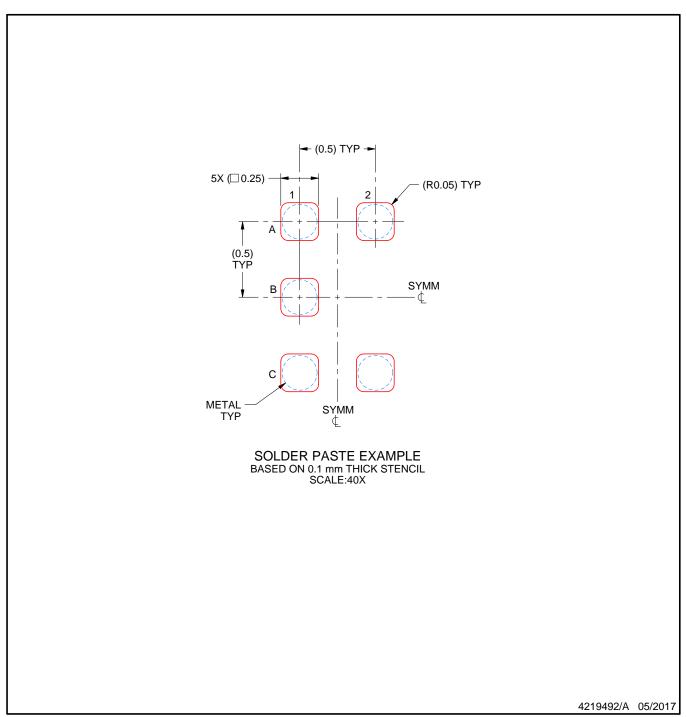
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

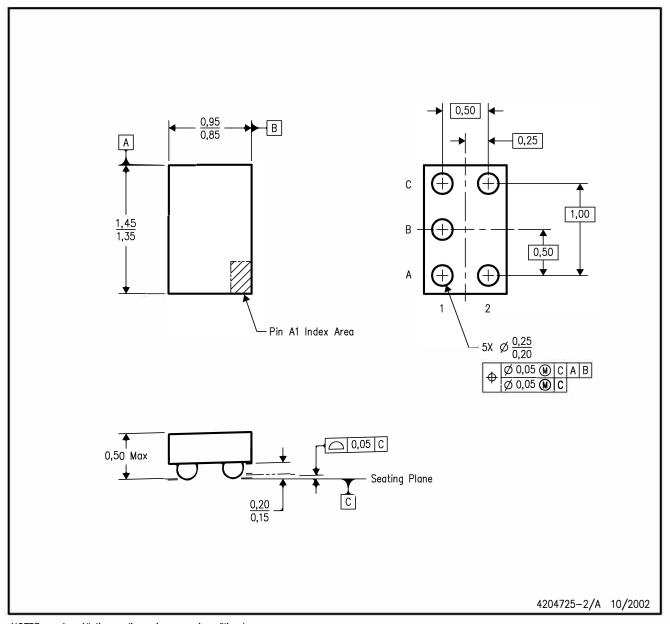


NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

YEP (R-XBGA-N5)

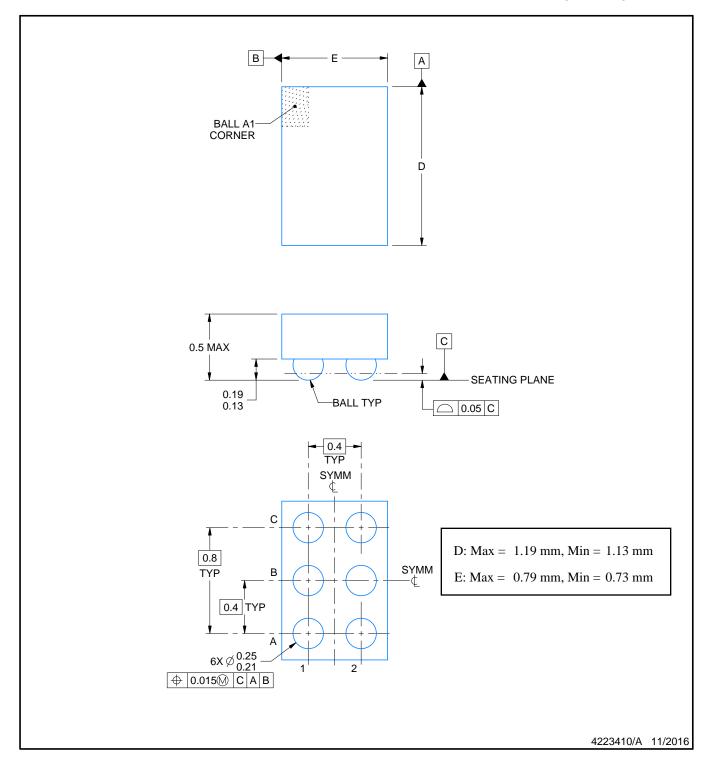
DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

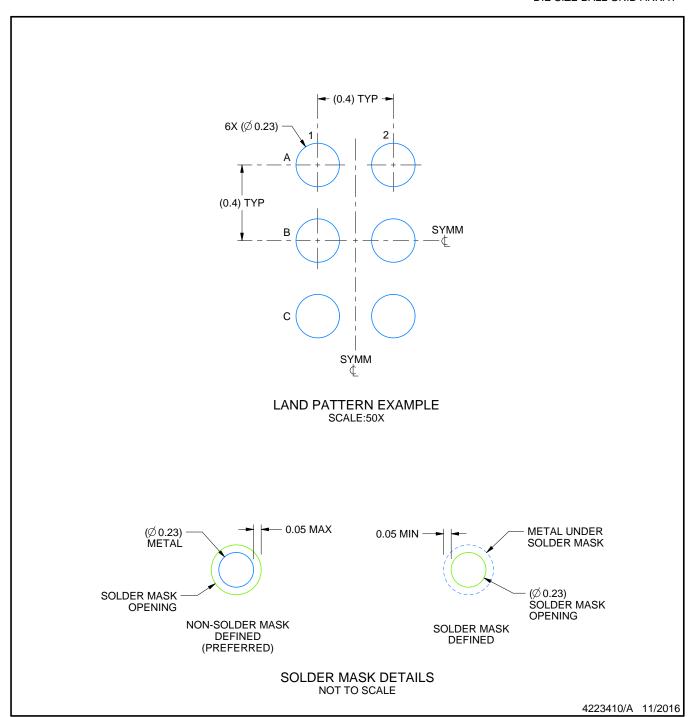
- B. This drawing is subject to change without notice.
- C. NanoStar™ package configuration.
- D. This package is tin-lead (SnPb). Refer to the 5 YZP package (drawing 4204741) for lead-free.





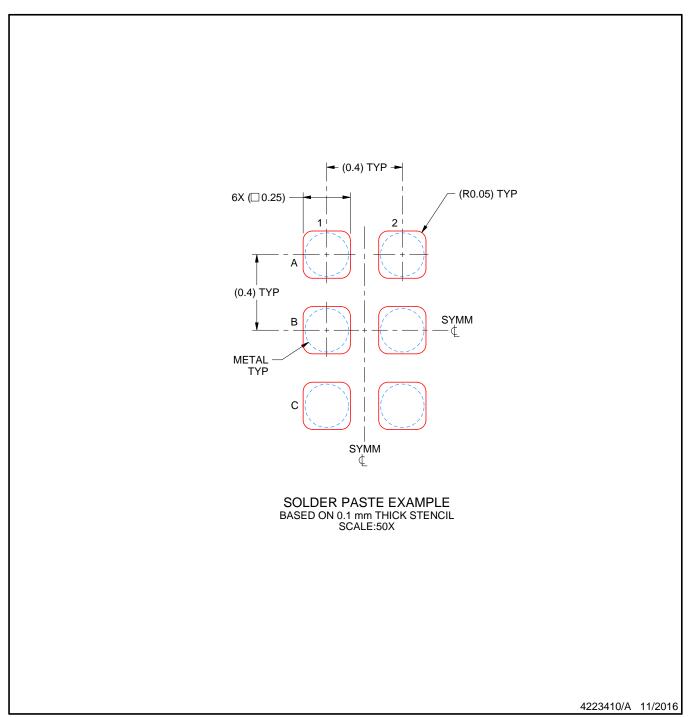
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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